

IGBT, T2 / T3 / IGBT, T2 / T3

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	950	V
Implementierter Kollektor-Strom Implemented collector current		I_{CN}	400	A
Kollektor-Dauergleichstrom Continuous DC collector current	$T_H = 65^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	I_{CDC}	380	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_p = 1\text{ ms}$	I_{CRM}	800	A
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

		min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 150\text{ A}$ $V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	1,07 1,04 1,02	1,14 V V V
Gate-Schwellenspannung Gate threshold voltage	$I_C = 6,50\text{ mA}, V_{CE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		V_{GETH}	4,15 4,90	5,65 V
Gateladung Gate charge	$V_{GE} = -15 / 15\text{ V}, V_{CE} = 600\text{ V}$		Q_G	4,10	μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,75	Ω
Eingangskapazität Input capacitance	$f = 100\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	49,2	nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 100\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,228	nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 950\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	I_{CES}		0,07 mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		100 nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 3,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,189 0,191 0,192	μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 3,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,026 0,032 0,034	μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 3,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,76 0,92 0,94	μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 3,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,23 0,44 0,49	μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}, L\sigma = 35\text{ nH}$ $di/dt = 5200\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Gon} = 3,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	3,10 4,00 4,30	mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}, L\sigma = 35\text{ nH}$ $du/dt = 1200\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Goff} = 3,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	24,5 35,3 37,9	mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 600\text{ V}$ $V_{CE\max} = V_{CES} - L_{SCE} \cdot di/dt$	$t_p \leq 0\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}	1200	A
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro IGBT / per IGBT		R_{thJH}	0,200	K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150 $^{\circ}\text{C}$

IGBT, T5 / T6 / IGBT, T5 / T6

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	950	V
Implementierter Kollektor-Strom Implemented collector current		I_{CN}	200	A
Kollektor-Dauergleichstrom Continuous DC collector current	$T_H = 65^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	I_{CDC}	140	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_p = 1\text{ ms}$	I_{CRM}	400	A
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

		min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 150\text{ A}$ $V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	1,68 1,88 1,92	1,98 V V V
Gate-Schwellenspannung Gate threshold voltage	$I_C = 3,25\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GETH}	4,35	5,10 5,85 V
Gateladung Gate charge	$V_{GE} = -15 / 15\text{ V}, V_{CE} = 600\text{ V}$		Q_G	0,45	μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	1,5	Ω
Eingangskapazität Input capacitance	$f = 100\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	12,6	nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 100\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,039	nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 950\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	I_{CES}		0,05 mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		100 nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 3,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,086 0,095 0,096	μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 3,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,02 0,022 0,023	μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 3,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,18 0,22 0,23	μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 3,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,032 0,089 0,112	μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}, L\sigma = 35\text{ nH}$ $di/dt = 5300\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Gon} = 3,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	5,00 6,43 6,79	mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 150\text{ A}, V_{CE} = 500\text{ V}, L\sigma = 35\text{ nH}$ $du/dt = 6000\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Goff} = 3,9\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	3,73 6,35 7,26	mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 600\text{ V}$ $V_{CE\max} = V_{CES} - L_{SCE} \cdot di/dt$	$t_p \leq 0\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}	600	A
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro IGBT / per IGBT		R_{thJH}	0,340	K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150 $^{\circ}\text{C}$